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## Unit 8 - Week 7 : Bipolar Junction Transistors

### Course outline

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Bipolar

### Assignment 7

The due date for submitting this assignment has passed.

As per our records you have not submitted this assignment.

**Due on 2018-09-19, 23:59 IST.**

1) Which of the following statements is true with regards to the BJT ?

**1 point**

- ☐ The base width must be designed to be much larger than the minority carrier diffusion length
- ☐ The base width must be designed to be much smaller than the minority carrier diffusion length
- ☐ The base region should be heavily doped
- ☐ None of the above

**No, the answer is incorrect.**

**Score: 0**

**Accepted Answers:**

*The base width must be designed to be much smaller than the minority carrier diffusion length*

2) Which of the following represents the Base Transport Factor for a pnp-BJT ?

**1 point**

- ☐  $\frac{I_{pC}}{I_{pE}}$
- ☐  $\frac{I_{nC}}{I_{nE}}$
- ☐  $\frac{I_{pE}}{I_{nE} + I_{pE}}$
- ☐  $\frac{I_C}{I_E}$

**No, the answer is incorrect.**

**Score: 0**

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☐ Quiz :  
Assignment 7

☐ Assignment 7:  
Solution

**Week 8 : Metal  
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**Week 10:  
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**Week 12: Thin  
Film Transistors  
(TFTs), Tutorial  
Sessions**

ce De

- ☐ 7.5  $\mu\text{A}$
- ☐ 0.33 mA
- ☐ 17 mA
- ☐ 82  $\mu\text{A}$

No, the answer is incorrect.

Score: 0

Accepted Answers:

0.33 mA

4) To bias a BJT in the saturation mode, Base-Emitter Junction is \_\_\_\_\_ biased and Collector-Base junction is \_\_\_\_\_ biased. **1 point**

- ☐ reverse, reverse
- ☐ reverse, forward
- ☐ forward, reverse
- ☐ forward, forward

No, the answer is incorrect.

Score: 0

Accepted Answers:

forward, forward

5) Consider that the base transport factor in BJT is given by:  $\alpha_T = \frac{1}{\cosh(\frac{x_B}{L_B})}$ , where  $x_B$  is **1 point**

the base-width and  $L_B$  is the minority carrier diffusion length in base. Find out the base-width needed in a pnp BJT to achieve a base transport factor of  $\alpha_T = 0.9967$ . Assume diffusion coefficient is  $10 \text{ cm}^2/\text{s}$  and minority carrier lifetime in base is  $10^{-7} \text{ s}$

- ☐ 0.81  $\mu\text{m}$
- ☐ 2.35  $\mu\text{m}$
- ☐ 0.2  $\mu\text{m}$
- ☐ None of the above

No, the answer is incorrect.

Score: 0

Accepted Answers:

0.81  $\mu\text{m}$

6) In a BJT biased in the active mode, the base current is 6  $\mu\text{A}$ , and the collector current is 510  $\mu\text{A}$ . Find the value of  $\alpha$ . **1 point**

- ☐ 0.5
- ☐ 0.92
- ☐ 0.988
- ☐ 0.965

No, the answer is incorrect.

Score: 0

Accepted Answers:

0.988

7) Which of the following in the BJT is the heavily doped region ? **1 point**

- ☐ Emitter

- ☐ Base
- ☐ Collector
- ☐ All the regions are equally doped

No, the answer is incorrect.

Score: 0

Accepted Answers:

*Emitter*

8) Base-width modulation in a BJT results in:

1 point

- ☐ an increase in output conductance of the device
- ☐ a decrease in output conductance of the device
- ☐ no change in output conductance
- ☐ none of the above

No, the answer is incorrect.

Score: 0

Accepted Answers:

*an increase in output conductance of the device*

9) A BJT is generally biased in \_\_\_\_\_ mode of operation in analog amplifier circuits.

1 point

- ☐ saturation
- ☐ cut-off
- ☐ inverse-active
- ☐ active

No, the answer is incorrect.

Score: 0

Accepted Answers:

*active*

10) Early voltage represents the voltage at which:

1 point

- ☐ break-down occurs at the junctions.
- ☐ saturation of collector current begins.
- ☐

curves on collector-current characteristics intersect the voltage axis, when extrapolated to zero collector current value.

- ☐ none of the above

No, the answer is incorrect.

Score: 0

Accepted Answers:

*curves on collector-current characteristics intersect the voltage axis, when extrapolated to zero collector current value.*

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